

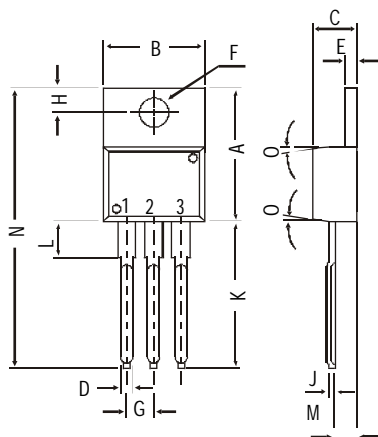
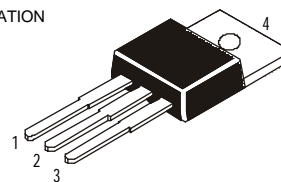
TO-220 Plastic Package

**2N6486, 2N6487, 2N6488
2N6489, 2N6490, 2N6491**

*2N6486, 6487, 6488 NPN PLASTIC POWER TRANSISTORS
2N6489, 6490, 6491 PNP PLASTIC POWER TRANSISTORS
General Purpose Amplifier and Switching Applications*

PIN CONFIGURATION

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR



DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
O	DEG 7	

All dimensions in mm.

ABSOLUTE MAXIMUM RATINGS

		6486	6487	6488	
		6489	6490	6491	
Collector-base voltage (open emitter)	V_{CBO} max.	50	70	90	V
Collector-emitter voltage (open base)	V_{CEO} max.	40	60	80	V
Collector current	I_C max.		15		A
Total power dissipation up to $T_C = 25^\circ C$	P_{tot} max.		75		W
Junction temperature	T_j max.		150		$^\circ C$
Collector-emitter saturation voltage	V_{CEsat} max.		1.3		V
$I_C = 5 A; I_B = 0.5 A$					
D.C. current gain	h_{FE} min.		20		
$I_C = 5 A; V_{CE} = 4 V$					
	h_{FE} max.		150		

RATINGS (at $T_A=25^\circ C$ unless otherwise specified)

		6486	6487	6488	
		6489	6490	6491	
Collector-base voltage (open emitter)	V_{CBO} max.	50	70	90	V
Collector-emitter voltage (open base)	V_{CEO} max.	40	60	80	V
Emitter-base voltage (open collector)	V_{EBO} max.		5.0		V

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Collector current	I_C	max.	15	A
Base current	I_B	max.	5.0	A
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_{tot}	max.	75	W
Derate above 25°C		max.	0.6	$W^\circ\text{C}$
Total power dissipation up to $T_A = 25^\circ\text{C}$	P_{tot}	max.	1.8	W
Derate above 25°C		max.	0.014	$W^\circ\text{C}$
Junction temperature	T_j	max.	150	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j-a}$		70	$^\circ\text{C/W}$
From junction to case	$R_{th\ j-c}$		1.67	$^\circ\text{C/W}$

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

**6486 6487 6488
6489 6490 6491**

Collector cutoff current				
$I_B = 0; V_{CE} = 20\text{ V}$	I_{CEO}	max.	1.0	- - mA
$I_B = 0; V_{CE} = 30\text{ V}$	I_{CEO}	max.	- 1.0	- mA
$I_B = 0; V_{CE} = 40\text{ V}$	I_{CEO}	max.	- - 1.0	mA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 45\text{ V}$	I_{CEX}	max.	500	- - μA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 65\text{ V}$	I_{CEX}	max.	- 500	- μA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 85\text{ V}$	I_{CEX}	max.	- - 500	μA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 40\text{ V}; T_C = 150^\circ\text{C}$	I_{CEX}	max.	5.0	- - mA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 60\text{ V}; T_C = 150^\circ\text{C}$	I_{CEX}	max.	- 5.0	- mA
$V_{EB(off)} = 1.5\text{ V}; V_{CE} = 80\text{ V}; T_C = 150^\circ\text{C}$	I_{CEX}	max.	- - 5.0	mA
Emitter cut-off current				
$I_C = 0; V_{EB} = 5\text{ V}$	I_{EBO}	max.	1.0	mA
Breakdown voltages				
$I_C = 200\text{ mA}; I_B = 0$	$V_{CEO(sus)}^*$	min.	40 60 80	V
$I_C = 1\text{ mA}; I_E = 0$	V_{CBO}	min.	50 70 90	V
$I_C = 200\text{ mA}; V_{BE} = 1.5\text{ V}$	$V_{CEX(sus)}^*$	min.	50 70 90	V
$I_E = 1\text{ mA}; I_C = 0$	V_{EBO}	min.	5.0	V
Saturation voltages				
$I_C = 5\text{ A}; I_B = 0.5\text{ A}$	V_{CEsat}^*	max.	1.3	V
$I_C = 15\text{ A}; I_B = 5\text{ A}$	V_{CEsat}^*	max.	3.5	V
Base-emitter on voltage				
$I_C = 5\text{ A}; V_{CE} = 4\text{ V}$	$V_{BE(on)}^*$	max.	1.3	V
$I_C = 15\text{ A}; V_{CE} = 4\text{ V}$	$V_{BE(on)}^*$	max.	3.5	V
D.C. current gain				
$I_C = 5\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}^*	min.	20	
		max.	150	
$I_C = 15\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}^*	min.	5.0	
Transition frequency				
$I_C = 1\text{ A}; V_{CE} = 4\text{ V}; f = 1\text{ MHz}$	$f_T(1)$	min.	5.0	MHz
Small signal current gain				
$I_C = 1.0\text{ A}; V_{CE} = 4\text{ V}; f = 1.0\text{ KHz}$	h_{fe}	min.	25	

* Pulse test: pulse width $\leq 300\ \mu\text{s}$; duty cycle $\leq 2\%$

(1) $f_T = |h_{fe}| \cdot f_{test}$

Notes

Disclaimer

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